



Drafts

Pending

Active

- L1: (259) memory and substrate and trench and memory near cell\$1 and trench near line
- L2: (187) memory and substrate and trench and memory near cell\$1 and trench near line and gate an...
- L3: (59) memory near flash and substrate and trench and memory near cell\$1 and trench near line a...
- L4: (4) memory near flash and substrate and trench and memory near cell\$1 and trench adj line and...
- L5: (16) memory and substrate and trench and memory near cell\$1 and trench adj line and gate and...
- L6: (6) memory near flash and substrate and trench adj line
- L7: (13) (first adj2 column) with trench

Failed

Saved

Favorites

Tagged (0)

UDC

Queue

Trash

Search

List

Browse

Queue

Clear

DBs US-PGPUB: USPAT: USI Plurals

Default operator: OR  Highlight all hit terms initially

(first adj2 column) with trench

BRS form

IS&amp;R form

Image

Text

HTML

U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	US 20050123257 A1	20050609	11	Optical fiber of complex index profile	385/127	
2	<input checked="" type="checkbox"/>	US 20050017283 A1	20050127		Semiconductor device	257/301	
3	<input checked="" type="checkbox"/>	US 20030180020 A1	20030925		Optical fiber of complex index profile	385/127	
4	<input checked="" type="checkbox"/>	US 20030169629 A1	20030911		Semiconductor memory cell configuration and a method for producing the configuration	365/200	257/E21.652
5	<input checked="" type="checkbox"/>	US 20030096429 A1	20030522		Laser-induced cell lysis system	436/174	422/99; 436/63
6	<input checked="" type="checkbox"/>	US 6904216 B2	20050607		Optical fiber of complex index profile	385/127	
7	<input checked="" type="checkbox"/>	US 6853023 B2	20050208		Semiconductor memory cell configuration and a method for producing the configuration	257/301	257/302; 257/774; 257/E21.652;
8	<input checked="" type="checkbox"/>	US 6815209 B2	20041109		Laser-induced cell lysis system	436/63	422/99; 435/287.1; 435/29;
9	<input checked="" type="checkbox"/>	US 6566691 B1	20030520		Semiconductor device with trench gate having structure to promote conductivity modulation	257/139	257/133; 257/330; 257/E21.384;
10	<input checked="" type="checkbox"/>	US 5529944 A	19960625		Method of making cross point four square folded bitline trench DRAM cell	438/242	257/E21.652; 257/E27.096; 438/246
11	<input checked="" type="checkbox"/>	US 5173436 A	19921222		Method of manufacturing an EEPROM with trench-isolated bitlines	438/262	257/E21.209; 257/E21.552; 257/E21.68

&lt; &gt; RE\_UTM

&gt; eDAN 1.6.1 -...

EAST - [107...

EAST Brow...

EAST Brow...

Document3 -...

Inbox - Micro...